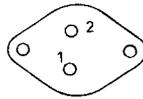
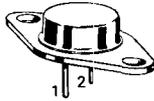


ALPHANUMERIC INDEX — CROSS-REFERENCE (Continued)

Industry Part Number	Motorola Direct Replacement	Motorola Similar Replacement	Page Number	Industry Part Number	Motorola Direct Replacement	Motorola Similar Replacement	Page Number
2N6283	2N6283		3-172	2N6323		MJ10015	3-606
2N6283JAN	2N6283JAN		3-172	2N6324		MJ10015	3-606
2N6283JTX	2N6283JTX		3-172	2N6325		MJ10015	3-606
2N6283JTXV	2N6283JTXV		3-172	2N6326	2N6328		—
2N6284	2N6284		3-172	2N6327	2N6328		—
2N6284JAN	2N6284JAN		3-172	2N6328	2N6328		—
2N6284JTX	2N6284JTX		3-172	2N6329		2N5884	3-127
2N6284JTXV	2N6284JTXV		3-172	2N6330		2N5884	3-127
2N6285	2N6285		3-172	2N6331		2N5884	3-127
2N6286	2N6286		3-172	2N6338	2N6338		3-188
2N6286JAN	2N6286JAN		3-172	2N6338JAN	2N6338JAN		3-188
2N6286JTX	2N6286JTX		3-172	2N6338JTX	2N6338JTX		3-188
2N6286JTXV	2N6286JTXV		3-172	2N6338JTXV	2N6338JTXV		3-188
2N6287	2N6287		3-172	2N6339	2N6339		3-188
2N6287JAN	2N6287JAN		3-172	2N6340	2N6340		3-188
2N6287JTX	2N6287JTX		3-172	2N6341	2N6341		3-188
2N6287JTXV	2N6287JTXV		3-172	2N6341JAN	2N6341JAN		3-188
2N6288	2N6288		3-151	2N6341JTX	2N6341JTX		3-188
2N6289		2N6288	3-151	2N6341JTXV	2N6341JTXV		3-188
2N6290	2N6292		3-151	2N6354		2N6339	3-188
2N6291	2N6292		3-151	2N6355		2N6057	3-143
2N6292	2N6292		3-151	2N6356		2N6057	3-143
2N6293		2N6292	3-151	2N6357		2N6058	3-143
2N6294	2N6294		3-177	2N6358		2N6058	3-143
2N6295	2N6295		3-177	2N6359		2N5885	3-127
2N6296	2N6296		3-177	2N6371		2N3055	3-6
2N6297	2N6297		3-177	2N6372		2N5428	3-101
2N6298	2N6298		3-147	2N6373		2N5428	3-101
2N6298JAN	2N6298JAN		3-147	2N6374		2N5428	3-101
2N6298JTX	2N6298JTX		3-147	2N6377	2N6377		3-191
2N6298JTXV	2N6298JTXV		3-147	2N6378	2N6378		3-191
2N6299	2N6299		3-147	2N6378JAN	2N6378JAN		3-191
2N6299JAN	2N6299JAN		3-147	2N6378JTX	2N6378JTX		3-191
2N6299JTX	2N6299JTX		3-147	2N6378JTXV	2N6378JTXV		3-191
2N6299JTXV	2N6299JTXV		3-147	2N6379	2N6379		3-191
2N6300	2N6300		3-147	2N6379JAN	2N6379JAN		3-191
2N6300JAN	2N6300JAN		3-147	2N6379JTX	2N6379JTX		3-191
2N6300JTX	2N6300JTX		3-147	2N6379JTXV	2N6379JTXV		3-191
2N6300JTXV	2N6300JTXV		3-147	2N6380		2N6377	3-191
2N6301	2N6301		3-147	2N6381		2N6378	3-191
2N6301JAN	2N6301JAN		3-147	2N6382		2N6379	3-191
2N6301JTX	2N6301JTX		3-147	2N6383	2N6383		3-195
2N6301JTXV	2N6301JTXV		3-147	2N6383JAN	2N6383JAN		3-195
2N6302		2N6303	3-105	2N6383JTX	2N6383JTX		3-195
2N6303	2N6303		3-32	2N6383JTXV	2N6383JTXV		3-195
2N6306	2N6306		3-181	2N6384	2N6384		3-195
2N6306JAN	2N6306JAN		3-181	2N6384JAN	2N6384JAN		3-195
2N6306JTX	2N6306JTX		3-181	2N6384JTX	2N6384JTX		3-195
2N6307	2N6307		3-181	2N6384JTXV	2N6384JTXV		3-195
2N6308	2N6308		3-181	2N6385	2N6385		3-195
2N6308JAN	2N6308JAN		3-181	2N6385JAN	2N6385JAN		3-195
2N6308JTX	2N6308JTX		3-181	2N6385JTX	2N6385JTX		3-195
2N6312	2N6318		3-185	2N6385JTXV	2N6385JTXV		3-191
2N6313		2N6318	3-185	2N6386	2N6386		3-199
2N6314		2N6318	3-185	2N6387	2N6387		3-199
2N6315		2N5428	3-101	2N6388	2N6388		3-199
2N6316		2N5428	3-101	2N6406		MJE171	3-862
2N6317	2N6317		3-185	2N6407		MJE172	3-862
2N6318	2N6318		3-185	2N6408		MJE181	3-862
2N6322		MJ10015	3-606	2N6409		MJE182	3-862

*Consult Motorola if a direct replacement is necessary.

TABLE 3 — METAL TO-213 (Formerly TO-66)



STYLE 1:
 PIN 1. BASE
 2. EMITTER
 CASE. COLLECTOR

CASE 80-02 (TO-213AA)

I _C Cont Amps Max	V _{CE0} (sus) Volts Min	Device Type		hFE Min/Max	@ I _C Amp	Resistive Switching			f _T MHz Min	P _D (Case) Watts @ 25°C
		NPN	PNP			t _s μs Max	t _f μs Max	@ I _C Amp		
1	80	2N4912		20/100	0.5	0.6 typ	0.3 typ	0.5	3	25
	175	2N3583	2N6420	40/200	0.5	2 typ	0.23 typ	0.5	10	35
	225	2N3738		40/200	0.1	3 typ	0.3 typ	0.1	10	20
	300	2N3739		40/200	0.1	3 typ	0.3 typ	0.1	10	20
2	225		2N6211	10/100	1	2.5	0.6	1	20	35
	250	2N3584	2N6421	25/100	1	4	3	1	10	35
	300	2N3585 2N4240	2N6212	10/100	1	2.5	0.6	1	20	35
			2N6422	25/100	1	4	3	1	10	35
350		2N6213	30/150	0.75	6	3	0.75	15	35	
3	140	2N3441		25/100	0.5				0.2	25
4	60	2N3054.A 2N3766 2N6294##	2N3740	30/100	0.25	1.3 typ	0.27 typ	0.25	4	25
				25/100	0.5	1 typ	0.3 typ	0.5	3	75
				40/160	0.5	0.9 typ	0.09 typ	0.5	10	20
			2N6296##	750/18k	2	0.9 typ	0.7 typ	2	4#	50
	80	2N3767 2N6295##	2N3741	30/100	0.25	1.3 typ	0.27 typ	0.25	4	25
				40/160	0.5	0.9 typ	0.09 typ	0.5	10	20
		2N6297##	750/18k	2	0.9 typ	0.7 typ	2	4	50	
5	80	2N4233A		25/100	1.5	0.5 typ	0.2 typ	1.5	4	75
7	60		2N6317	20/100	2.5	1	0.8	2.5	4	90
	80	2N5428		60/240	2	2	0.2	2	30	40
			2N6318	20/100	2.5	1	0.8	2.5	4	90
	100	2N5429 2N5430		30/120 60/240	2 2	2 2	0.2 0.2	2 2	30 30	40 40
8	60	2N6300##	2N6298##	750/18k	4	1.5 typ	1.5 typ	4	4#	75
	80	2N6301##	2N6299##	750/18k	4	1.5 typ	1.5 typ	4	4#	75

|h_{FE}| @ 1 MHz, ## Darlington

JAN, JTX, JTXV Available

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TABLE 12 — POWER DARLINGTONS (continued)

I _C Cont Amps Max	V _{CEO(sus)} Volts Min	Device Type		hFE Min/Max	@ I _C Amp	Resistive Switching			h _{FE} @ 1 MHz Min	P _D (Case) Watts @ 25°C	Case JEDEC/MOT
		NPN	PNP			t _s μs Max	t _f μs Max	@ I _C Amp			
		4	40			MJE3300 2N6037	MJE3310 2N6034	1k min 750/1k			
	45	BD675 BD675A	BD676 BD676A BD776	750 min 750 min 750 min	1.5 2 2				20	40 40 15	TO-225AA/77 TO-225AA/77 TO-225AA/77
	60	BD677 BD677A BD777 MJE3301 MJE800 MJE800T MJE801 2N6038 2N6294	BD678 BD678A BD778 MJE700 MJE700T MJE701 2N6035 2N6296	750 min 750 min 750 min 1k min 750 min 750 min 750 min 750/18k 750/18k	1.5 2 2 1 1.5 1.5 2 2 2	1.7 typ 0.9 typ	1.2 typ 0.7 typ	2 2	20 20 1 1 1 25 4	15 40 40 15 40 40 40 40 50	TO-225AA/77 TO-225AA/77 TO-225AA/77 TO-225AA/77R TO-225AA/77 TO-220/221A TO-225AA/77 TO-225AA/77 TO-213AA/80
	80	BD679 BD679A BD779 MJD6039 MJE802 MJE803 2N6039 2N6295	BD680 BD680A BD780 MJD6036 MJE702 MJE703 2N6036 2N6297	750 min 750 min 750 min 1k/12k 750 min 750 min 750/18k 750/18k	1.5 2 2 2 1.5 2 2 2	1.7 typ 1.7 typ 0.9 typ	1.2 typ 1.2 typ 0.7 typ	2 2	20 25 40 40 25 4	40 40 15 20 40 40 40 50	TO-225AA/77 TO-225AA/77 TO-225AA/77 TO-252/369A-04 TO-225AA/77 TO-225AA/77 TO-225AA/77 TO-213AA/80
	100	BD681	BD682	750 min	1.5					40	TO-225AA/77
5	60	MJE1100 MJE1101 TIP120	MJE1090 MJE1091 TIP125	750 min 750 min 1k min	3A 4A 3	1.5 typ	1.5 typ	3	1 1 4	70 70 65	TO-225AB/90 TO-225AB/90 TO-220/221A
	80	MJE1102 MJE1103 TIP121	MJE1092 MJE1102 TIP126	750 min 750 min 1k min	3A 4A 3	1.5 typ	1.5 typ	3	1 1 4	70 70 65	TO-225AB/90 TO-225AB/90 TO-220/221A
	100	MJF122 TIP122	MJF127 TIP127	2k min 1k min	3 3	1.5 typ 1.5 typ	1.5 typ 1.5 typ	3 3	4 4	28 65	—/221C-02 TO-220/221A
7	300	MJ3041		250 min	2.5					100	TO-204/1
	350	MJ3042		250 min	2.5					100	TO-204/1
	375	BU522		250 min	2.5				7.5	75	TO-220/221A
	425	BU522A		250 min	2.5				7.5	75	TO-220/221A
	450	BU522B		250 min	2.5				7.5	75	TO-220/221A
8	40	2N6386		1k/20k	3				20	65	TO-220/221A
	45	BDX53 BD895 BD895A	BDX54 BD896 BD896A	750 min 750 min 750 min	3 3 4				4 1 1	60 70 70	TO-220/221A TO-220/221A TO-220/221A
	60	BDX53A BD897 BD897A MJ1000 TIP100 2N6043 2N6300 2N6055 MJE6043	BDX54A BD898 BD898A MJ900 TIP105 2N6040 2N6298 2N6053 MJE6040	750 min 750 min 750 min 1k min 1k/20k 1k/10k 750k/18k 750k/18k 1k/20k	3 3 4 3 3 4 4 4 4	1.5 typ 1.5 typ 1.5 typ	1.5 typ 1.5 typ 1.5 typ	3 3 4 4 4 4 2	4 1 1 90 80 75 4 100 75	60 70 70 90 80 75 4 100 75	TO-220/221A TO-220/221A TO-220/221A TO-204/1 TO-220/221A TO-220/221A TO-213AA/80 TO-204/1 TO-225AB/90
	80	BDX53B BD899 BD899A	BDX54B BD900 BD900A	750 min 750 min 750 min	3 3 4				4 1 1	60 70 70	TO-220/221A TO-220/221A TO-220/221A

(continued)

MOTOROLA
SEMICONDUCTOR
TECHNICAL DATA

2N6053, 2N6054
2N6298, 2N6299 PNP
2N6055, 2N6056
2N6300, 2N6301 NPN

DARLINGTON COMPLEMENTARY SILICON POWER TRANSISTORS

... designed for general-purpose amplifier and low frequency switching applications.

- High DC Current Gain —
 $h_{FE} = 3000$ (Typ) @ $I_C = 4.0$ Adc
- Collector-Emitter Sustaining Voltage — @ 100 mA
 $V_{CE(sus)} = 60$ Vdc (Min) — 2N6053, 2N6055, 2N6298, 2N6300
 $= 80$ Vdc (Min) — 2N6054, 2N6056, 2N6299, 2N6301
- Low Collector-Emitter Saturation Voltage —
 $V_{CE(sat)} = 2.0$ Vdc (Max) @ $I_C = 4.0$ Adc
 $= 3.0$ Vdc (Max) @ $I_C = 8.0$ Adc
- Monolithic Construction with Built-in Base-Emitter Shunt Resistors

***MAXIMUM RATINGS**

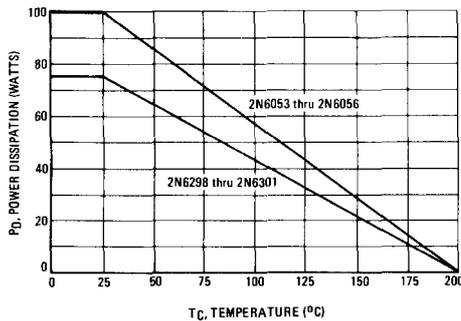
Rating	Symbol	2N6053 2N6055 2N6298 2N6300	2N6054 2N6056 2N6299 2N6301	Unit
Collector-Emitter Voltage	V_{CEO}	60	80	Vdc
Collector-Base Voltage	V_{CB}	60	80	Vdc
Emitter-Base Voltage	V_{EB}	5.0		Vdc
Collector Current — Continuous Peak	I_C	8.0 16		Adc
Base Current	I_B	120		mAdc
Total Device Dissipation @ $T_C = 25^\circ\text{C}$ Derate above 25°C	P_D	100 0.571	75 0.428	Watts $\text{W}/^\circ\text{C}$
Operating and Storage Junction Temperature Range	T_J, T_{stg}	-65 to +200		$^\circ\text{C}$

THERMAL CHARACTERISTICS

Characteristic	Symbol	2N6053 2N6054 2N6055 2N6056	2N6298 2N6299 2N6300 2N6301	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	1.75	2.33	$^\circ\text{C}/\text{W}$

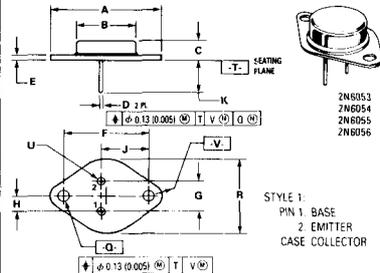
*Indicates JEDEC Registered Data.

FIGURE 1 — POWER DERATING



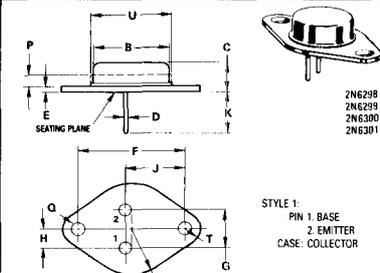
DARLINGTON 8 AMPERE COMPLEMENTARY SILICON POWER TRANSISTORS

60-80 VOLTS
75,100 WATTS



DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	—	29.37	—	1.150
B	—	21.08	—	0.830
C	6.35	8.25	0.250	0.325
D	0.97	1.09	0.038	0.043
E	1.40	1.77	0.055	0.070
F	30.15 BSC	—	1.187 BSC	—
G	10.92 BSC	—	0.430 BSC	—
H	5.46 BSC	—	0.215 BSC	—
J	16.89 BSC	—	0.665 BSC	—
K	11.13	12.19	0.440	0.480
Q	3.81	4.19	0.151	0.165
R	—	26.67	—	1.050
U	4.83	5.33	0.190	0.210
V	3.81	4.19	0.151	0.165

CASE 1-06
TO-204AA
(TO-3)



DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
B	11.84	12.70	0.470	0.500
C	6.35	8.64	0.250	0.340
D	3.71	0.96	0.028	0.034
E	1.27	1.91	0.050	0.075
F	24.33	24.43	0.958	0.962
G	4.83	5.33	0.190	0.210
H	2.41	2.67	0.095	0.105
J	14.48	14.99	0.570	0.590
K	3.14	—	0.360	—
P	—	1.27	—	0.050
Q	3.61	3.86	0.142	0.152
S	—	8.89	—	0.350
T	—	3.68	—	0.145
U	—	15.75	—	0.620

CASE 80-02
TO-213AA
(TO-66)

All JEDEC Dimensions and Notes Apply.

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2N6053, 2N6054, 2N6298, 2N6299 PNP, 2N6055, 2N6056, 2N6300, 2N6301 NPN

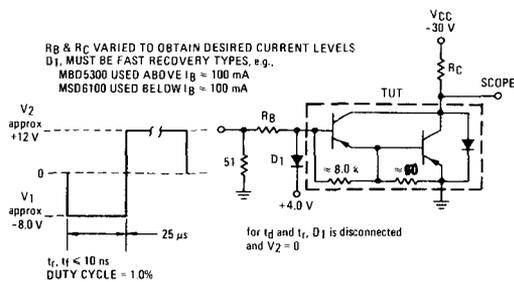
*ELECTRICAL CHARACTERISTICS ($T_C = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector-Emitter Sustaining Voltage (1) ($I_C = 100 \text{ mA dc}, I_B = 0$) 2N6053, 2N6055, 2N6298, 2N6300 2N6054, 2N6056, 2N6299, 2N6301	$V_{CE(sus)}$	60 80	— —	Vdc
Collector Cutoff Current ($V_{CE} = 30 \text{ Vdc}, I_B = 0$) ($V_{CE} = 40 \text{ Vdc}, I_B = 0$) 2N6053, 2N6055, 2N6298, 2N6300 2N6054, 2N6056, 2N6299, 2N6301	I_{CEO}	— —	0.5 0.5	mA dc
Collector Cutoff Current ($V_{CE} = \text{Rated } V_{CB}, V_{BE(off)} = 1.5 \text{ Vdc}$) ($V_{CE} = \text{Rated } V_{CB}, V_{BE(off)} = 1.5 \text{ Vdc}, T_C = 150^\circ\text{C}$)	I_{CEX}	— —	0.5 5.0	mA dc
Emitter Cutoff Current ($V_{BE} = 5.0 \text{ Vdc}, I_C = 0$)	I_{EBO}	—	2.0	mA dc
ON CHARACTERISTICS (1)				
DC Current Gain ($I_C = 4.0 \text{ A dc}, V_{CE} = 3.0 \text{ Vdc}$) ($I_C = 8.0 \text{ A dc}, V_{CE} = 3.0 \text{ Vdc}$)	h_{FE}	750 100	18000 —	—
Collector-Emitter Saturation Voltage ($I_C = 4.0 \text{ A dc}, I_B = 16 \text{ mA dc}$) ($I_C = 8.0 \text{ A dc}, I_B = 80 \text{ mA dc}$)	$V_{CE(sat)}$	— —	2.0 3.0	Vdc
Base-Emitter Saturation Voltage ($I_C = 8.0 \text{ A dc}, I_B = 80 \text{ mA dc}$)	$V_{BE(sat)}$	—	4.0	Vdc
Base-Emitter On Voltage ($I_C = 4.0 \text{ A dc}, V_{CE} = 3.0 \text{ Vdc}$)	$V_{BE(on)}$	—	2.8	Vdc
DYNAMIC CHARACTERISTICS				
Magnitude of Common Emitter Small-Signal Short Circuit Current Transfer Ratio ($I_C = 3.0 \text{ A dc}, V_{CE} = 3.0 \text{ Vdc}, f = 1.0 \text{ MHz}$)	$ h_{fe} $	4.0	—	—
Output Capacitance ($V_{CB} = 10 \text{ Vdc}, I_E = 0, f = 0.1 \text{ MHz}$) 2N6053, 2N6054, 2N6298, 2N6299 2N6055, 2N6056, 2N6300, 2N6301	C_{ob}	— —	300 200	pF
Small-Signal Current Gain ($I_C = 3.0 \text{ A dc}, V_{CE} = 3.0 \text{ Vdc}, f = 1.0 \text{ kHz}$)	h_{fe}	300	—	—

*Indicates JEDEC Registered Data.

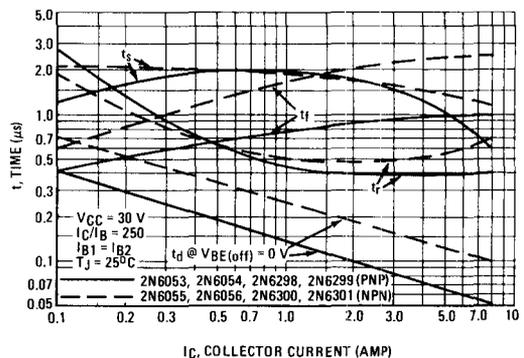
(1) Pulse Test: Pulse Width = 300 μs , Duty Cycle = 2.0 %.

FIGURE 2 – SWITCHING TIMES TEST CIRCUIT



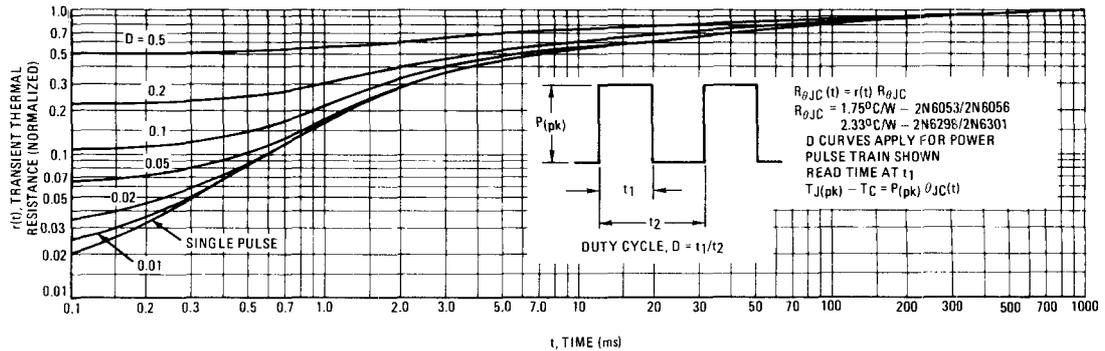
For NPN test circuit reverse diode, polarities and input pulses.

FIGURE 3 – SWITCHING TIMES



**2N6053, 2N6054, 2N6298, 2N6299 PNP,
2N6055, 2N6056, 2N6300, 2N6301 NPN**

FIGURE 4 – THERMAL RESPONSE



ACTIVE-REGION SAFE OPERATING AREA

FIGURE 5 – 2N6053 thru 2N6056

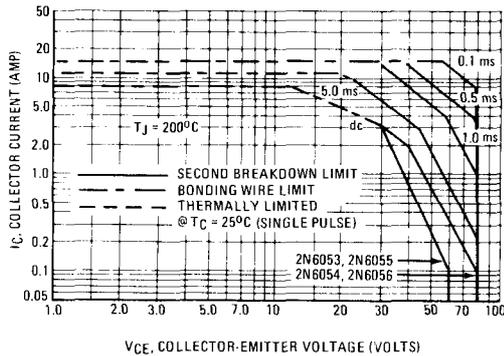
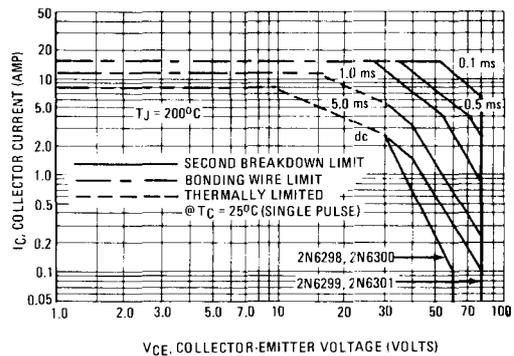


FIGURE 6 – 2N6298 thru 2N6301



3

There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate $I_C - V_{CE}$ limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate. The data of Figures 5 and 6 is based on $T_{J(pk)} = 200^{\circ}\text{C}$; T_C is

variable depending on conditions. Second breakdown pulse limits are valid for duty cycles to 10% provided $T_{J(pk)} \leq 200^{\circ}\text{C}$. $T_{J(pk)}$ may be calculated from the data in Figure 4. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.

FIGURE 7 – SMALL-SIGNAL CURRENT GAIN

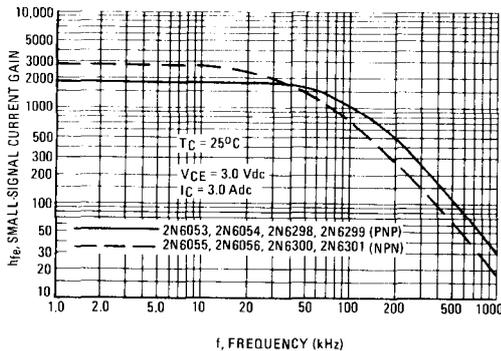
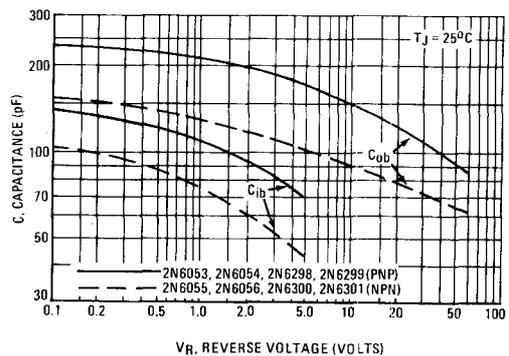


FIGURE 8 – CAPACITANCE



**2N6053, 2N6054, 2N6298, 2N6299 PNP,
2N6055, 2N6056, 2N6300, 2N6301 NPN**

PNP

2N6053, 2N6054, 2N6298, 2N6299

NPN

2N6055, 2N6056, 2N6300, 2N6301

FIGURE 9 – DC CURRENT GAIN

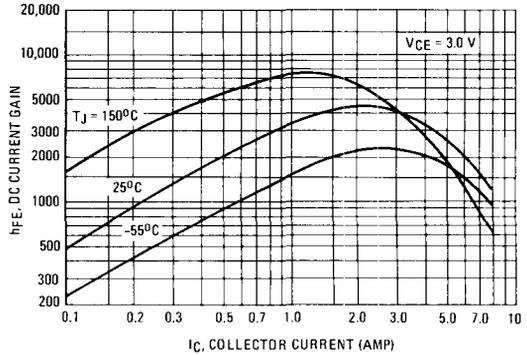
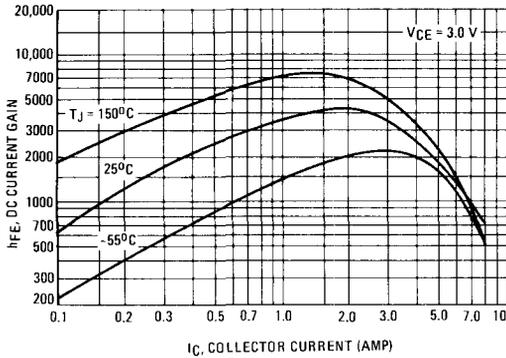


FIGURE 10 – COLLECTOR SATURATION REGION

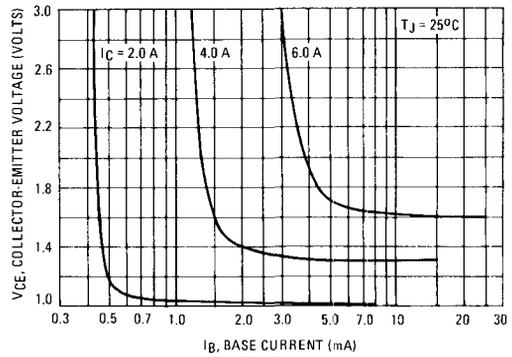
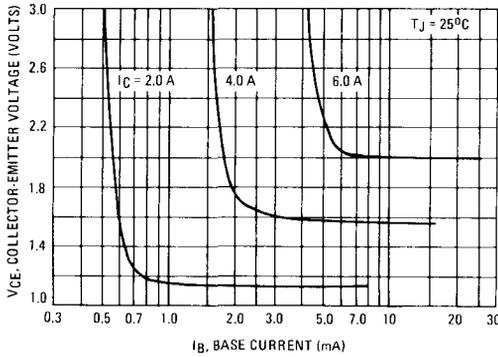
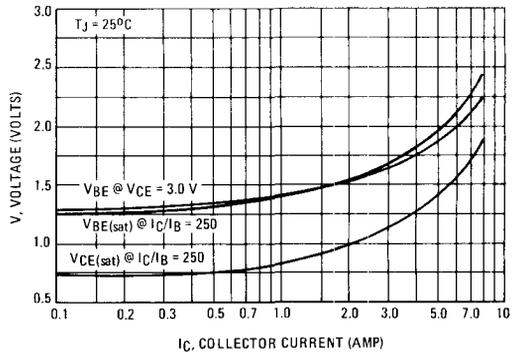
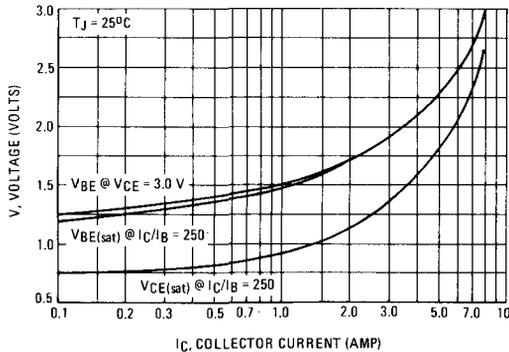


FIGURE 11 – "ON" VOLTAGES



3

2N6306
2N6307, 2N6308

HIGH VOLTAGE NPN SILICON POWER TRANSISTORS

... designed for high voltage inverters, switching regulators and line-operated amplifier applications. Especially well suited for switching power supply applications in associated consumer products.

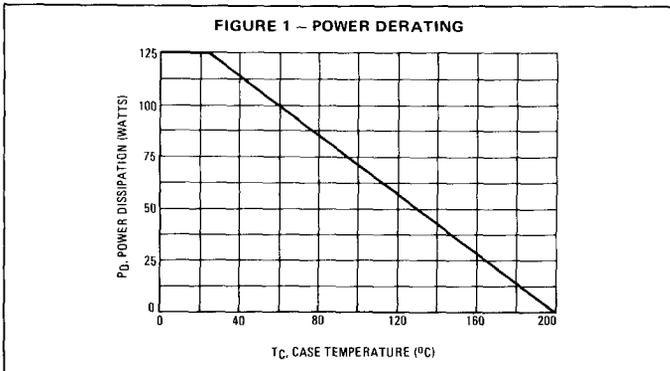
- High Collector-Base Voltage —
 $V_{CB} = 500 \text{ Vdc} - 2N6306$
 $= 600 \text{ Vdc} - 2N6307$
 $= 700 \text{ Vdc} - 2N6308$
- Excellent DC Current Gain @ $I_C = 3.0 \text{ Adc}$
 $h_{FE} = 15 - 75 - 2N6306, 2N6307$
 $= 12 - 60 - 2N6308$
- Low Collector-Emitter Saturation Voltage @ $I_C = 3.0 \text{ Adc}$
 $V_{CE(sat)} = 0.8 \text{ Vdc (Max)} - 2N6306$
 $= 1.0 \text{ Vdc (Max)} - 2N6307$
 $= 1.5 \text{ Vdc (Max)} - 2N6308$
- Current Gain Bandwidth Product —
 $f_T = 5.0 \text{ MHz (Min)} @ I_C = 0.3 \text{ Adc}$

***MAXIMUM RATINGS**

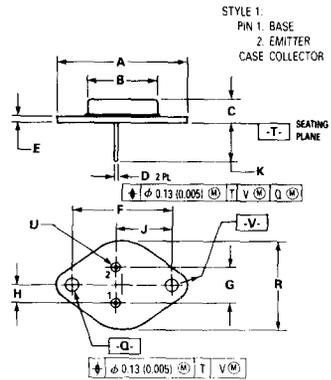
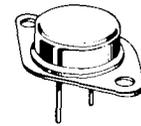
Rating	Symbol	2N6306	2N6307	2N6308	Unit
Collector-Base Voltage	V_{CB}	500	600	700	Vdc
Collector-Emitter Voltage	V_{CEO}	250	300	350	Vdc
Emitter-Base Voltage	V_{EB}	← 8.0 →			Vdc
Collector Current — Continuous Peak	I_C	← 8.0 → 16			A dc
Base Current	I_B	← 4.0 →			A dc
Total Device Dissipation @ $T_C = 25^\circ\text{C}$ Derate above 25°C	P_D	← 125 → 0.714			Watts W/ $^\circ\text{C}$
Operating and Storage Junction Temperature Range	T_J, T_{stg}	← -65 to +200 →			$^\circ\text{C}$

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	θ_{JC}	1.4	$^\circ\text{C/W}$

*Indicates JEDEC Registered Data.



8 AMPERE
POWER TRANSISTORS
NPN SILICON
250-300-350 VOLTS
125 WATTS



- NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.
 3. ALL RULES AND NOTES ASSOCIATED WITH REFERENCED TO-204AA OUTLINE SHALL APPLY.

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	—	39.37	—	1.560
B	—	21.08	—	0.830
C	6.35	8.25	0.250	0.325
D	0.97	1.09	0.038	0.043
E	1.40	1.77	0.055	0.070
F	30.15 BSC	—	1.187 BSC	—
G	10.92 BSC	—	0.430 BSC	—
H	5.46 BSC	—	0.215 BSC	—
J	16.89 BSC	—	0.665 BSC	—
K	11.78	12.19	0.460	0.480
Q	3.84	4.19	0.151	0.165
R	—	26.67	—	1.050
U	4.83	5.33	0.190	0.210
V	3.84	4.19	0.151	0.165

CASE 1-06
TO-204AA
(TO-3)

3